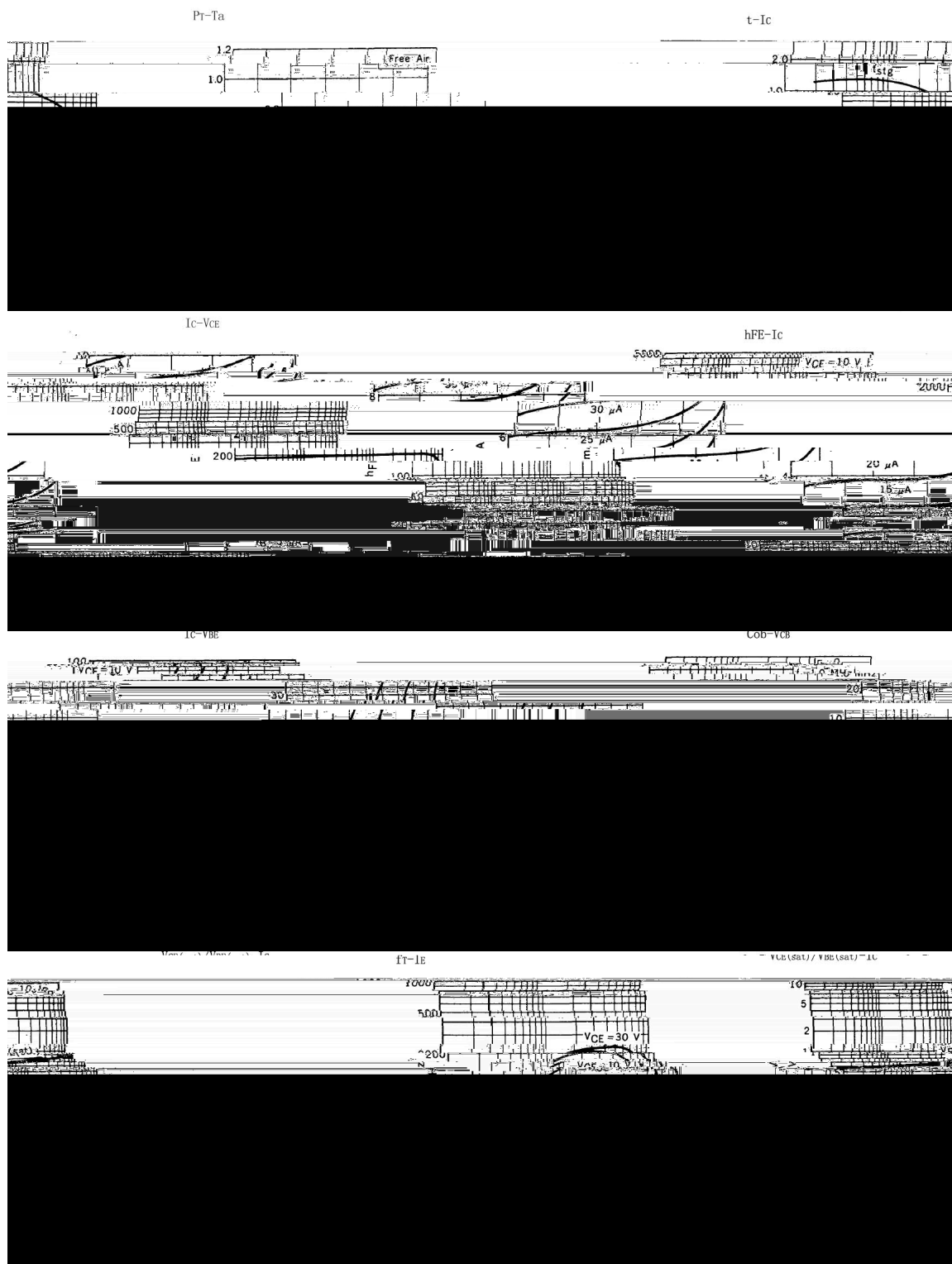


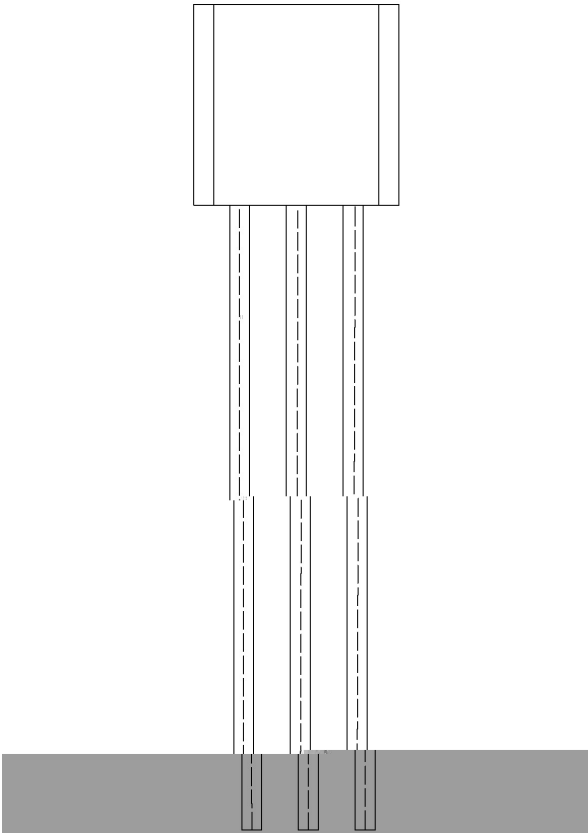
WR0<5 M M E QSQ æ M y s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

High breakdown voltage, good h_{FE} linearity, complementary to 2SA1376.

General purpose amplifier applications requiring high breakdown voltages.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	180	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Base Current - Continuous	I_B	20	mA
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		





Б " X

EU: 𐄂 𐄃 𐄄 𐄅

F67: ; X 𐄂 𐄃 𐄄 𐄅

0= 𐄂 k_{1H} 𐄆 𐄇

---- X 𐄂 𐄃 𐄄 𐄅 𐄆 𐄇 𐄈 𐄉 𐄊 𐄋 𐄌 𐄍 𐄎 𐄏 𐄐

Note:

BR: Company Code.

C3478: Product Type.

0= h



б " χ

- 1 ђ □ ѓ 25 Ѐ 150 † ђ ђ 60 Ѐ 90sec;
- 2 Š Œ □ ѓ 255 ° 5 † ђ ђ 'Y / ђ 5 ° 0.5sec;
- 3 і ђ , ђ ђ ѓ ђ 2 Ѐ 10 † /sec.

Note:

- 1.Preheating:25~150 † , Time:60~90sec.
- 2.Peak Temp.:255 ° 5 † , Duration:5 ° 0.5sec.
3. Cooling Speed: 2~10 † /sec.

□ ѓ χ 270 ° 5 † ђ ђ χ 10 ° 1 sec.

Temp:270±5 Time:10±1 sec

"Q T Y E / BULK

Package Type	Units	Dimension	(unit mm3)
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